

# BAV74LT1

## Monolithic Dual Switching Diode

### Features

- Pb-Free Packages are Available

### MAXIMUM RATINGS (EACH DIODE)

Rating	Symbol	Value	Unit
Reverse Voltage	$V_R$	50	Vdc
Forward Current	$I_F$	200	mAdc
Peak Forward Surge Current	$I_{FM(surge)}$	500	mAdc

### THERMAL CHARACTERISTICS

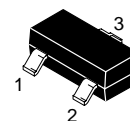
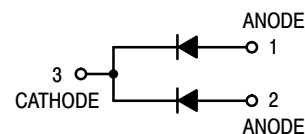
Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1), $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	225 1.8	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	$^\circ\text{C}/\text{W}$
Total Device Dissipation Alumina Substrate, (Note 2) $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	300 2.4	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- FR-5 =  $1.0 \times 0.75 \times 0.062$  in.
- Alumina =  $0.4 \times 0.3 \times 0.024$  in 99.5% alumina.

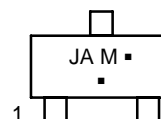


ON Semiconductor®



SOT-23  
CASE 318  
STYLE 9

### MARKING DIAGRAM



JA = Device Code  
M = Date Code\*  
▪ = Pb-Free Package

(Note: Microdot may be in either location)

\*Date Code orientation and/or overbar may vary depending upon manufacturing location.

### ORDERING INFORMATION

Device	Package	Shipping <sup>†</sup>
BAV74LT1	SOT-23	3000/Tape & Reel
BAV74LT1G	SOT-23 (Pb-Free)	3000/Tape & Reel
BAV74LT3	SOT-23	10,000/Tape & Reel
BAV74LT3G	SOT-23 (Pb-Free)	10,000/Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# BAV74LT1

## ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted) (EACH DIODE)

Characteristic	Symbol	Min	Max	Unit
<b>OFF CHARACTERISTICS</b>				
Reverse Breakdown Voltage ( $I_{(BR)} = 5.0 \mu\text{A}$ )	$V_{(BR)}$	50	–	Vdc
Reverse Voltage Leakage Current, (Note 3) ( $V_R = 50 \text{ Vdc}$ , $T_J = 125^\circ\text{C}$ ) ( $V_R = 50 \text{ Vdc}$ )	$I_R$	–	100 0.1	$\mu\text{A}$
Diode Capacitance ( $V_R = 0$ , $f = 1.0 \text{ MHz}$ )	$C_D$	–	2.0	pF
Forward Voltage ( $I_F = 100 \text{ mA}$ )	$V_F$	–	1.0	Vdc
Reverse Recovery Time ( $I_F = I_R = 10 \text{ mA}$ , $I_{R(REC)} = 1.0 \text{ mA}$ , measured at $I_R = 1.0 \text{ mA}$ , $R_L = 100 \Omega$ )	$t_{rr}$	–	4.0	ns

3. For each individual diode while the second diode is unbiased.

### Curves Applicable to Each Anode

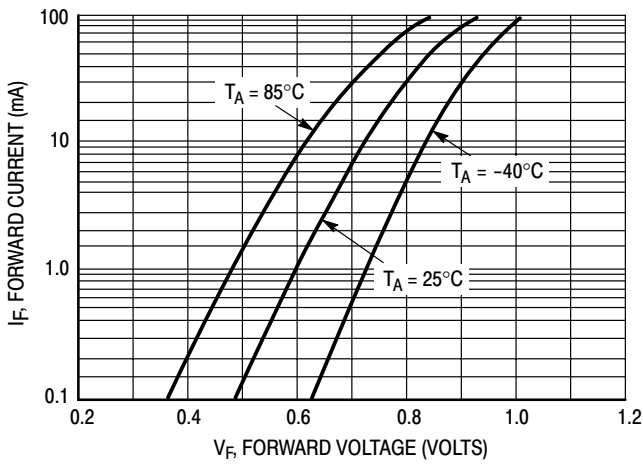


Figure 1. Forward Voltage

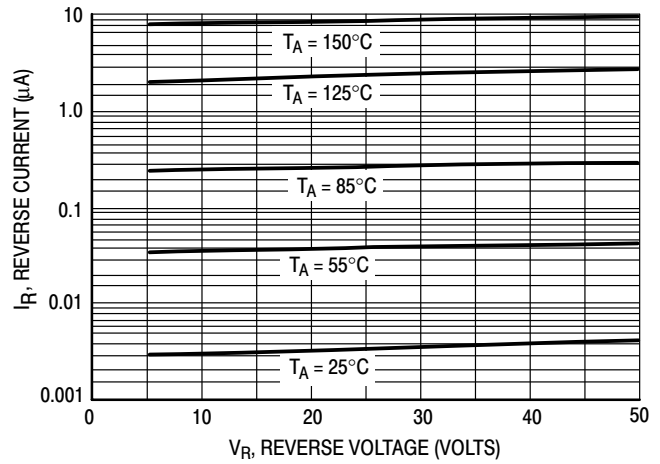


Figure 2. Leakage Current

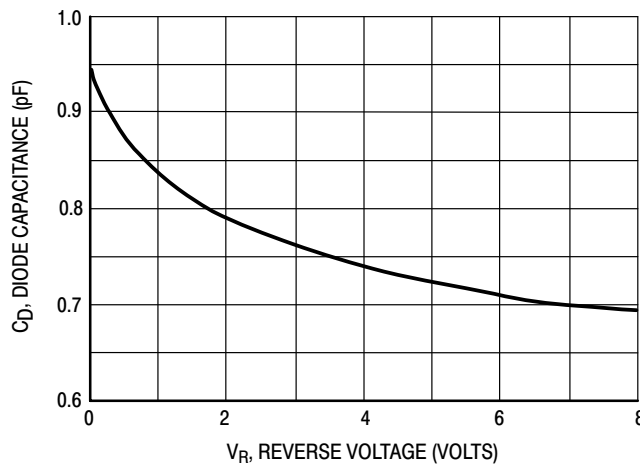
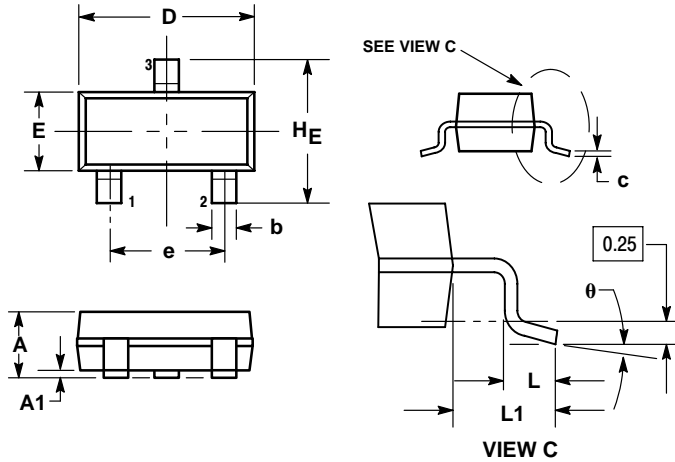


Figure 3. Capacitance

# BAV74LT1

## PACKAGE DIMENSIONS

SOT-23 (TO-236)  
CASE 318-08  
ISSUE AN



NOTES:

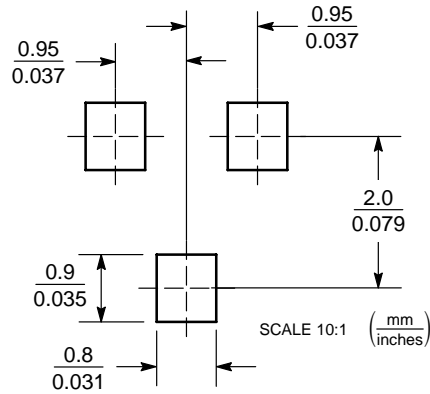
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. 318-01 THRU -07 AND -09 OBSOLETE, NEW STANDARD 318-08.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
c	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.081
L	0.10	0.20	0.30	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
HE	2.10	2.40	2.64	0.083	0.094	0.104

STYLE 9:

1. ANODE
2. ANODE
3. CATHODE

### SOLDERING FOOTPRINT\*



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.